

isc Silicon PNP Power Transistor

2N6421

DESCRIPTION

- Continuous Collector Current- $I_C = -2A$
- Power Dissipation- $P_C = 35W @ T_C = 25^\circ C$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -0.75 V(Max) @ I_C = -1A$

APPLICATIONS

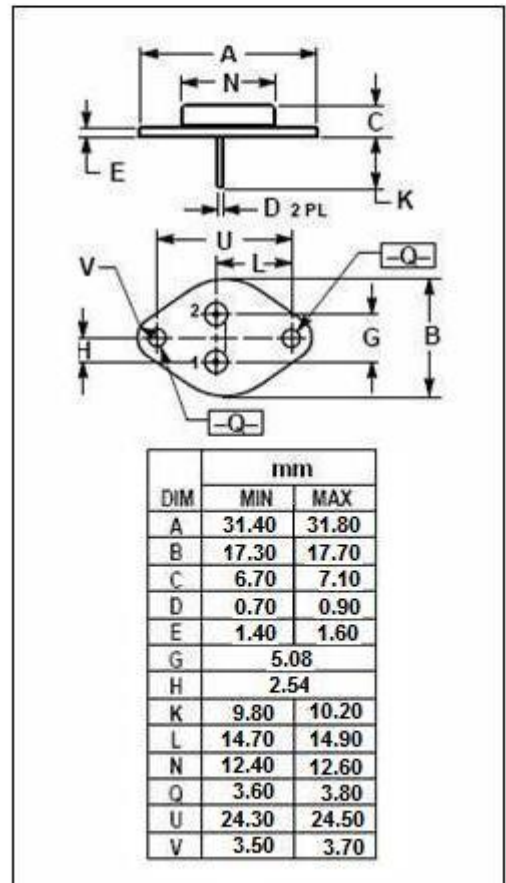
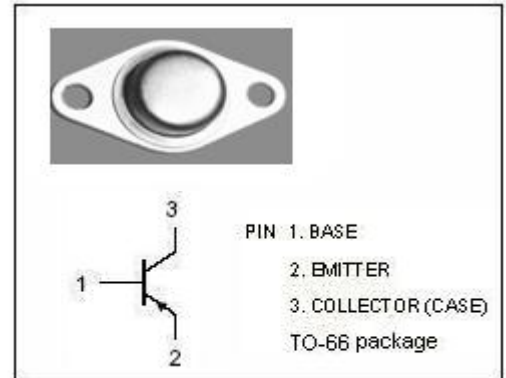
- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters, deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-375	V
V_{CEO}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2.0	A
I_{CM}	Collector Current-Peak	-5.0	A
I_B	Base Current	-1.0	A
P_C	Collector Power Dissipation@ $T_C = 25^\circ C$	35	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	5.0	$^\circ C/W$



isc Silicon PNP Power Transistor**2N6421****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -50\text{mA}; I_B = 0$	-250		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.125\text{A}$		-0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$		-1.4	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -10\text{V}$		-1.4	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -150\text{V}; I_B = 0$		-5.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$		-0.5	mA
h_{FE-1}	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -10\text{V}$	40		
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	8	80	
h_{FE-3}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -10\text{V}$	25	100	